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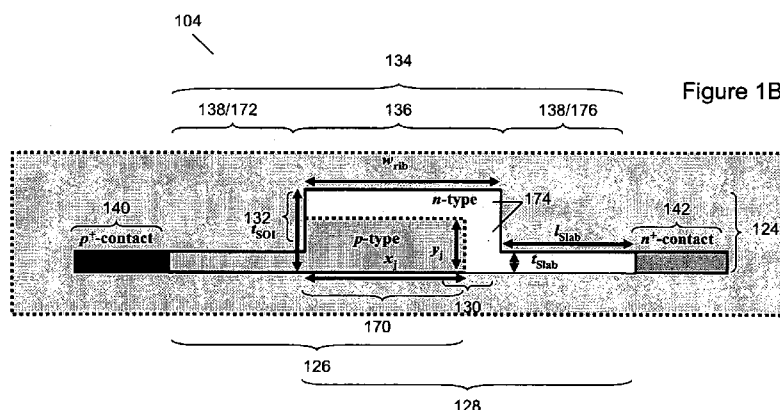
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(54) Title: A PHASE SHIFTING DEVICE AND A METHOD FOR MANUFACTURING THE SAME



(57) Abstract: In an embodiment, a phase shifting device may be provided. The phase shifting device may include a supporting layer and a semiconducting layer disposed above the supporting layer. The semiconducting layer may include a first doped region doped with doping atoms of a first conductivity type and arranged on the supporting layer; and a second doped region doped with doping atoms of a second conductivity type being different from the first conductivity type; wherein the second doped region may be disposed over the first doped region such that a first doped regions junction may be formed in a direction substantially parallel to a surface of the supporting layer and a second doped regions junction may be formed in a direction substantially perpendicular to the surface of the supporting layer. A method of forming a phase shifting device and an electro-optic device may also be provided.